

The ITZ35C12 is a very robust non punch through n-channel, enhancement mode insulated gate bipolar transistor (IGBT) designed for low power dissipation in a wide range of high voltage applications such as power supplies and motor drives. The high impedance gate simplifies gate drive considerations, allowing operation directly from low power control circuitry.

Fast rise and fall times allow very high frequency switching making the device suitable for modern systems employing high frequency switching.

Low saturation voltages minimise power dissipation, thereby reducing the cost of the overall system in which they are used.

The ITZ is fully short circuit rated making it especially suited for motor control and other applications requiring short circuit with stand capability. Each device in the Powerline range is available with or without an integral anti-parallel ultrafast soft recovery diode, see separate datasheet for discrete device

Typical applications include high frequency inverters for motor control, welding and heating apparatus. The Powerline range of IGBTs is also applicable to switched mode and uninterruptible power supplies.

FEATURES

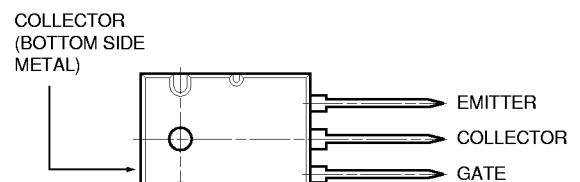
- Enhancement Mode n-Channel Device
- Non Punch Through Structure
- High Switching Speed
- Low On-state Saturation Voltage
- High Input Impedance Simplifies Gate Drive
- Latch-Free Operation
- Fully Short Circuit Rated To 10μs
- Square RBSOA
- Integral Fast Recovery Diode

APPLICATIONS

- High Frequency Inverters
- Motor Control
- Switched Mode Power Supplies
- High Frequency Welding
- Heating/Cooking Apparatus

KEY PARAMETERS

V_{CES}	(max)	1200V
$V_{CE(sat)}$	(typ)	2.7V
I_{C25}	(max)	65A
I_{C85}	(max)	35A
I_{CM}	(max)	105A
t_{sc}	(max)	10μs



Outline type code: TO264

(See Package Outlines for further information)

Fig.1 Pin connections - top view (not to scale)

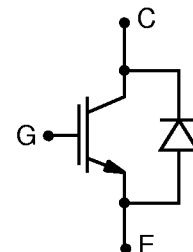


Fig.2 ITZ35C12 circuit

ORDERING INFORMATION

ITZ35C12T TO264 (with fast recovery diode)

Note: When ordering, use the complete part number.

ITZ35C12

ABSOLUTE MAXIMUM RATINGS

Stresses above those listed under 'Absolute Maximum Ratings' may cause permanent damage to the device.

T_{case} = 25°C unless stated otherwise.

Symbol	Parameter	Test Conditions	Max.	Units
V _{CES}	Collector-emitter voltage	V _{GE} = 0V	1200	V
V _{GES}	Gate-emitter voltage	-	±20	V
I _{C25}	Continuous collector current	T _{case} = 25°C	65	A
I _{C85}	Continuous collector current	T _{case} = 85°C	35	A
I _{CM}	Pulsed collector current	1ms, T _{case} = 85°C	105	A
P _{tot}	Power dissipation	T _{case} = 85°C	155	W

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Conditions	Min.	Max.	Units
R _{th(j-c)}	Thermal resistance - IGBT	DC junction to case	-	0.42	°C/W
R _{th(j-c)}	Thermal resistance - Diode	DC junction to case	-	0.7	°C/W
T _{OP}	Operating junction temperature range	-	−40	150	°C
T _{stg}	Storage temperature range	-	−40	150	°C
-	Mounting torque	M3 screw	-	1.1	Nm

DC ELECTRICAL CHARACTERISTICS

T_{case} = 25°C unless stated otherwise.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
I _{CES}	Collector cut-off current	V _{GE} = 0V, V _{CE} = 1200V	-	-	1	mA
I _{GES}	Gate leakage current	V _{GE} = 20V, V _{CE} = 0V	-	-	±500	nA
V _{GE(TH)}	Gate threshold voltage	I _C = 2mA, V _{CE} = V _{GE}	4.5	6	7.5	V
V _{CE(SAT)}	Collector-emitter saturation voltage	V _{GE} = 15V, I _C = 35A	-	2.7	3.3	V
		V _{GE} = 15V, I _C = 35A, T _j = 125°C	-	3.3	-	V

AC ELECTRICAL CHARACTERISTICS

 $T_{\text{case}} = 25^{\circ}\text{C}$ unless stated otherwise.

Symbol		Conditions	Min.	Typ.	Max.	Units
C_{ies}	Input capacitance	$V_{\text{CE}} = 25\text{V}$, $V_{\text{GE}} = 15\text{V}$, $f = 1\text{MHz}$	-	8040	-	pF
C_{oes}	Output capacitance	$V_{\text{CE}} = 25\text{V}$, $V_{\text{GE}} = 15\text{V}$, $f = 1\text{MHz}$	-	340	-	pF
C_{res}	Reverse transfer capacitance	$V_{\text{CE}} = 25\text{V}$, $V_{\text{GE}} = 15\text{V}$, $f = 1\text{MHz}$	-	90	-	pF

INDUCTIVE SWITCHING CHARACTERISTICS - see figures 3 to 5

 $T_{\text{case}} = 25^{\circ}\text{C}$ unless stated otherwise.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
$t_{\text{d(ON)}}$	Turn-on delay time	$I_{\text{C}} = 35\text{A}$, $V_{\text{GE}} = \pm 15\text{V}$, $V_{\text{CE}} = 50\% V_{\text{ces}}$ $R_{\text{G(ON)}} = 20\Omega$ $R_{\text{G(OFF)}} = 5\Omega$	-	75	-	ns
t_{r}	Rise time		-	45	-	ns
E_{ON}	Turn-on energy loss - per cycle		-	3.2	-	mJ
$t_{\text{d(OFF)}}$	Turn-off delay time		-	240	-	ns
t_{f}	Fall time		-	60	-	ns
E_{OFF}	Turn-off energy loss - per cycle		-	3.7	-	mJ

 $T_{\text{case}} = 125^{\circ}\text{C}$ unless stated otherwise.

$t_{\text{d(ON)}}$	Turn-on delay time	$I_{\text{C}} = 35\text{A}$, $V_{\text{GE}} = \pm 15\text{V}$, $V_{\text{CE}} = 50\% V_{\text{ces}}$ $R_{\text{G(ON)}} = 20\Omega$ $R_{\text{G(OFF)}} = 5\Omega$	-	75	-	ns
t_{r}	Rise time		-	50	-	ns
E_{ON}	Turn-on energy loss - per cycle		-	5.5	-	mJ
$t_{\text{d(OFF)}}$	Turn-off delay time		-	270	-	ns
t_{f}	Fall time		-	80	-	ns
E_{OFF}	Turn-off energy loss - per cycle		-	4.7	-	mJ

For additional switching information please refer to figures 8 to 13.

SHORT CIRCUIT RATING

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
t_{sc}	Short circuit withstand time	$T_{\text{c}} = 125^{\circ}\text{C}$, $V_{\text{GE}} = 15\text{V}$, $V_{\text{CE}} = 80\% V_{\text{CES}}$	-	-	10	μs

Caution: These devices are sensitive to electrostatic discharge. Users should observe proper ESD handling precautions.

DIODE CHARACTERISTICS

T_c = 25°C unless stated otherwise.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
V _{FM}	Forward voltage	At I _F = 35A peak	-	2.2	-	V
		At I _F = 35A peak, T _{case} = 125°C	-	2.2	-	V
t _{rr}	Reverse recovery time	I _F = 35A, di _{RR} /dt = 200A/μs	-	90	-	ns
I _{RRM}	Reverse recovery current	V _R = 50%V _{RRM}	-	15	-	A

BASIC TEST CIRCUIT AND SWITCHING DEFINITIONS

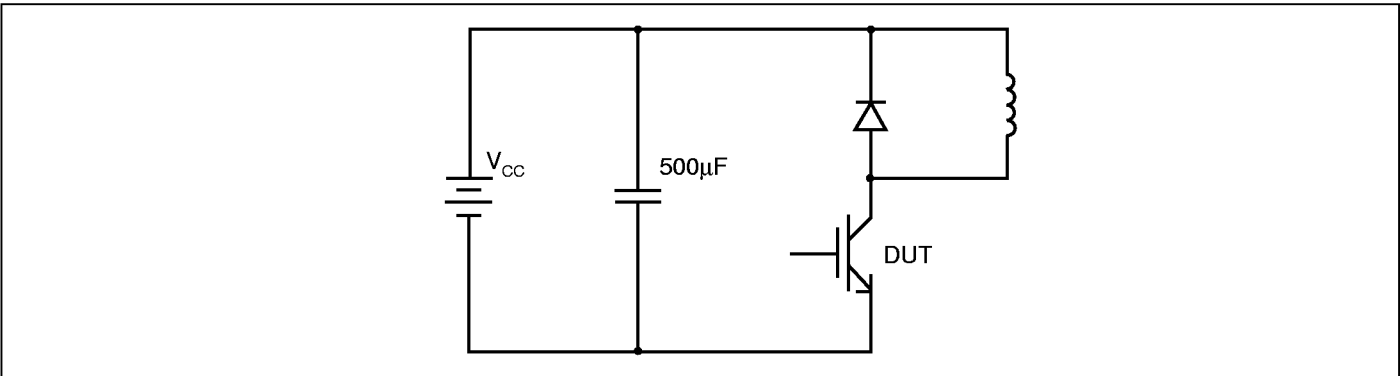


Fig.3 Basic d.c. chopper circuit

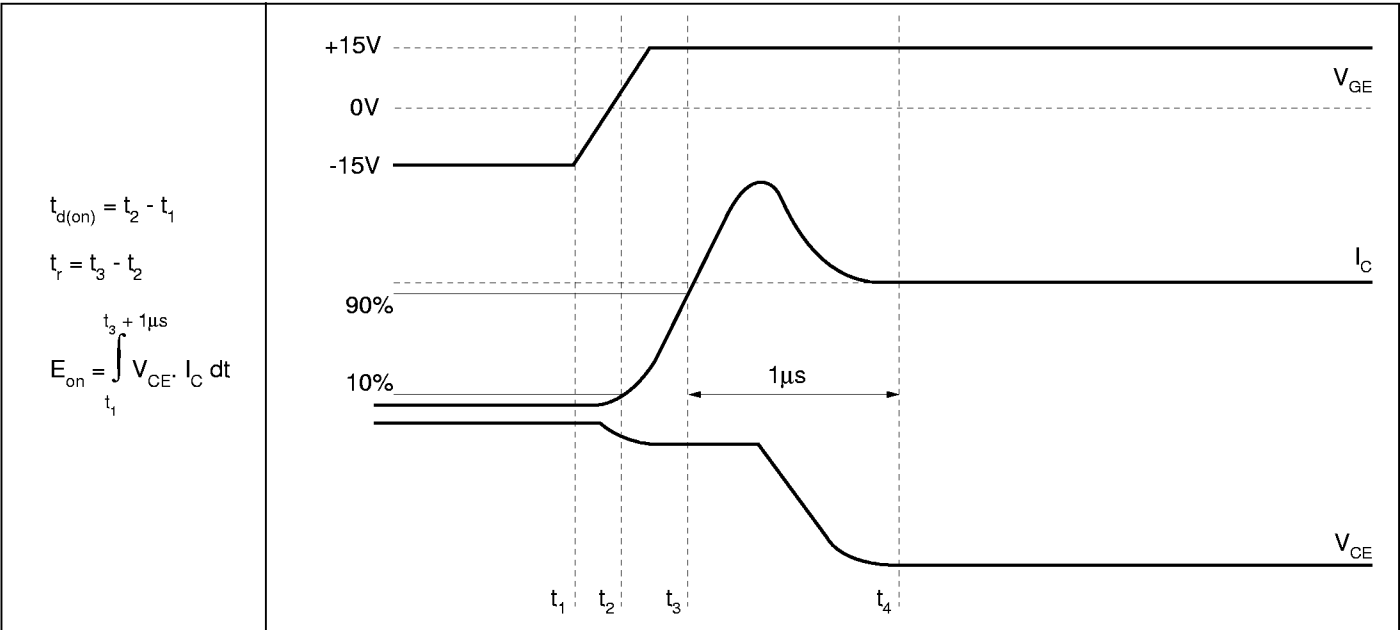


Fig.4 Turn-on characteristics

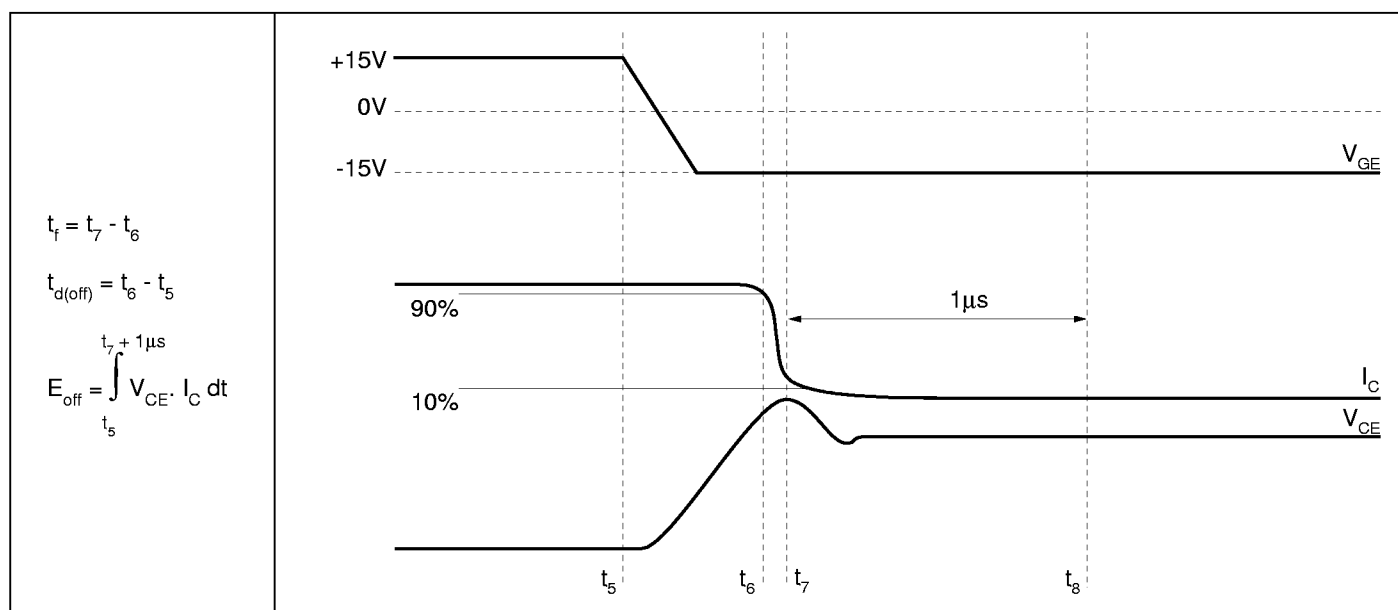


Fig.5 Turn-off characteristics

CURVES

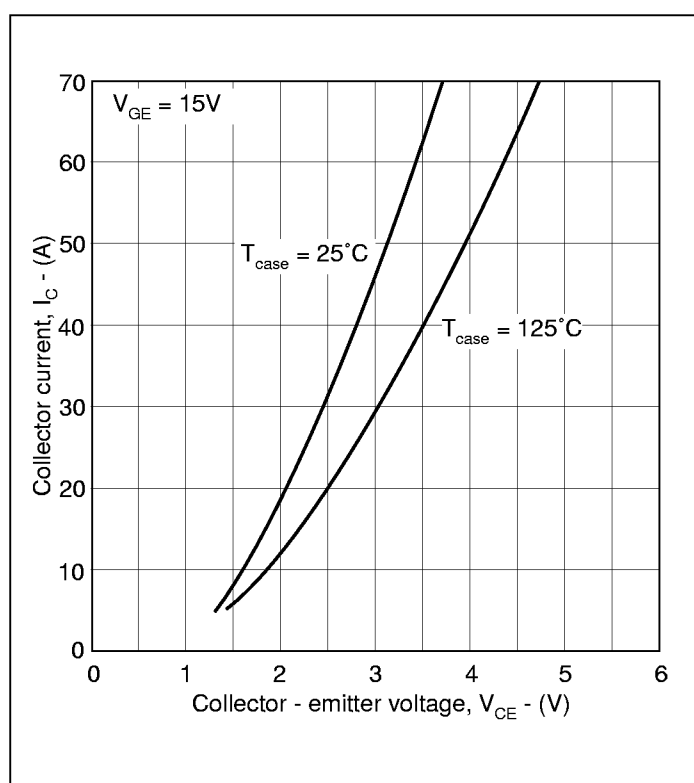


Fig.6 Typical output characteristics

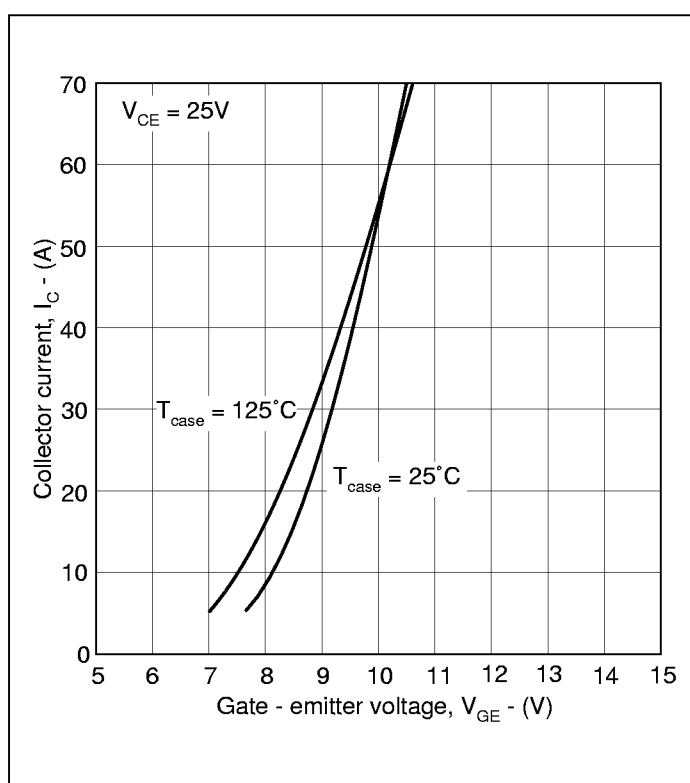


Fig.7 Typical transfer characteristics

Caution: These devices are sensitive to electrostatic discharge. Users should observe proper ESD handling precautions.

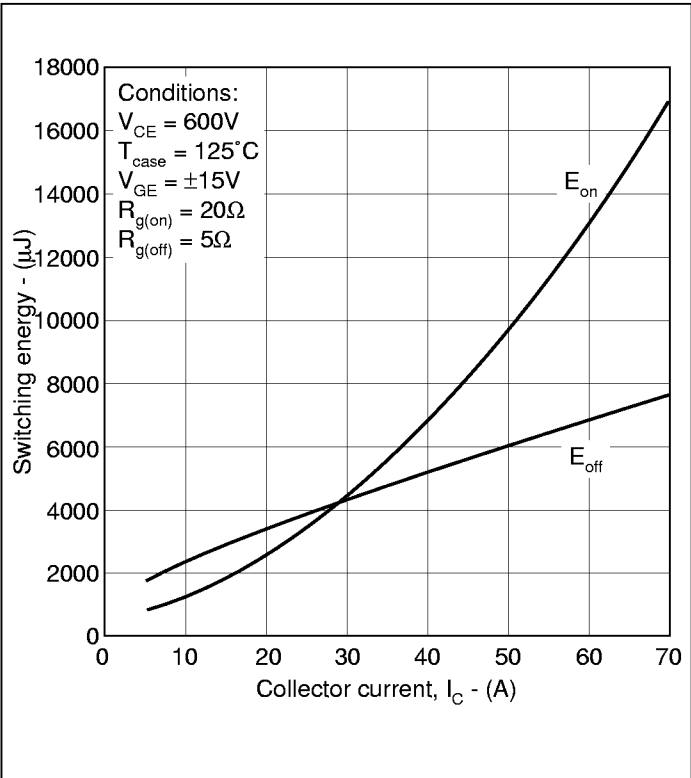


Fig.8 Typical switching losses vs collector current

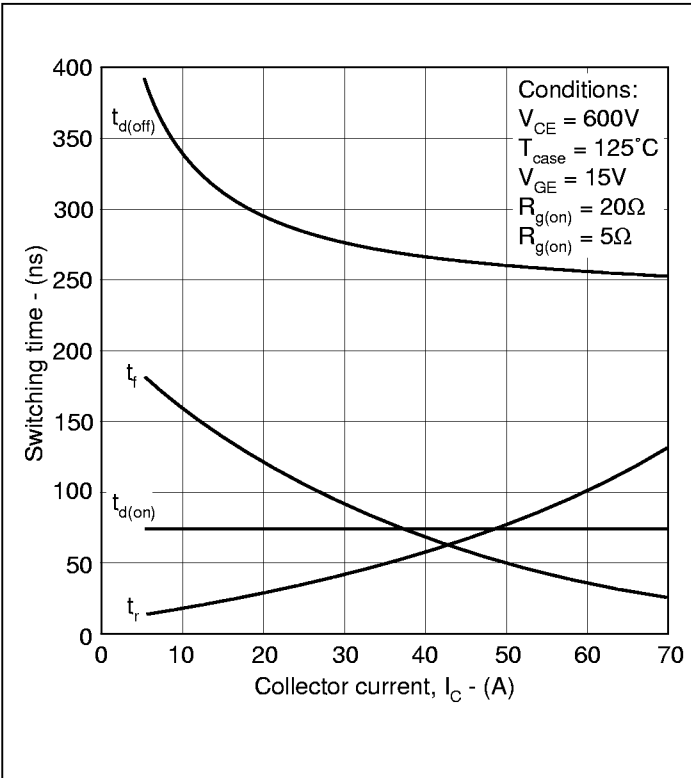


Fig.9 Typical switching times vs collector current

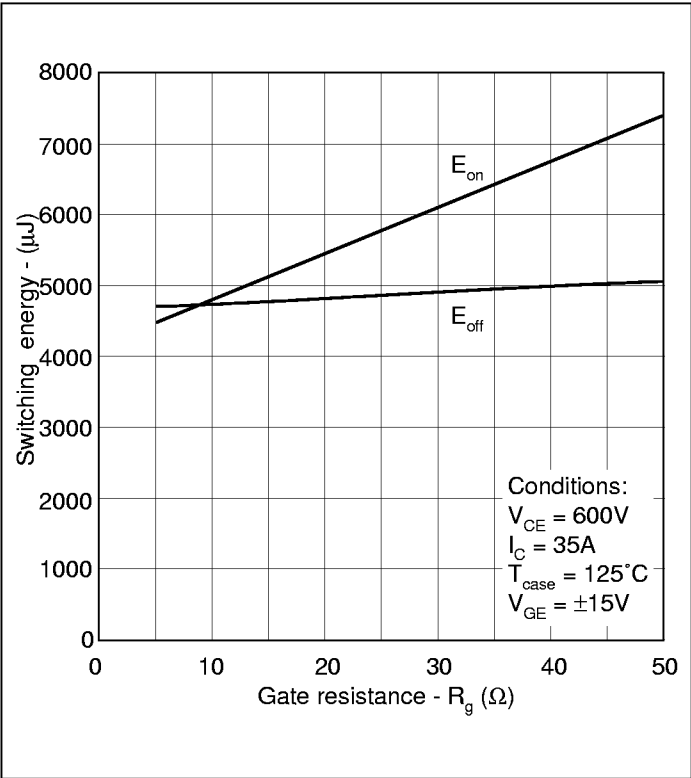


Fig.10 Typical switching losses vs gate resistance

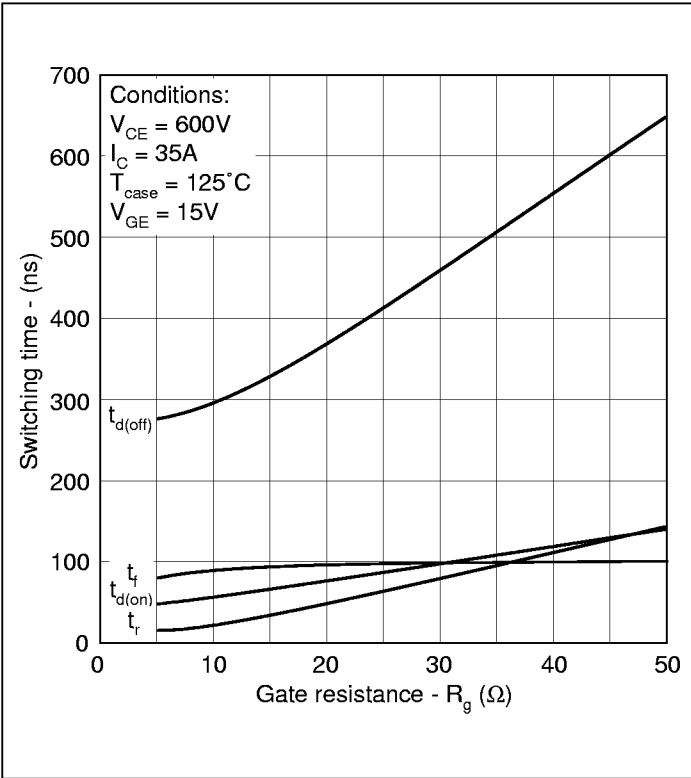


Fig.11 Typical switching times vs gate resistance

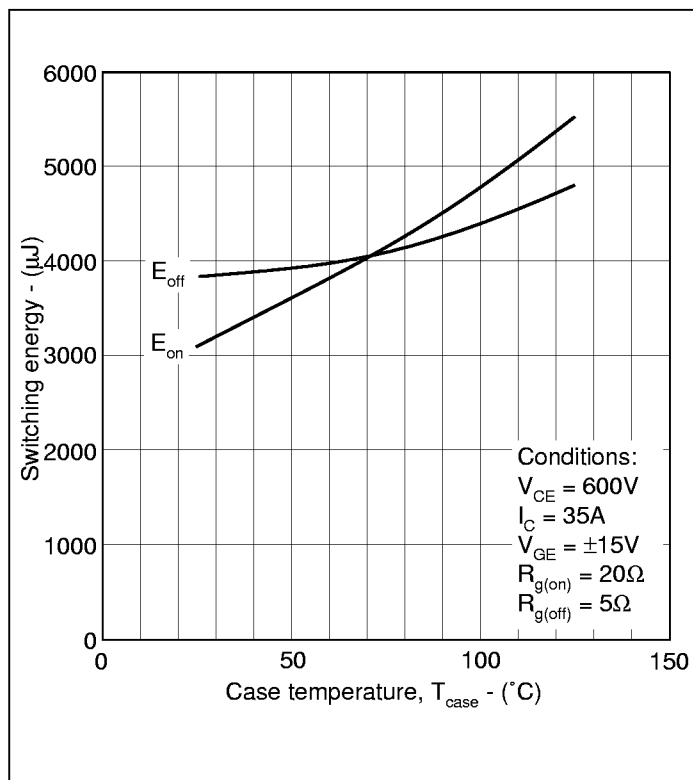


Fig.12 Typical switching losses vs case temperature

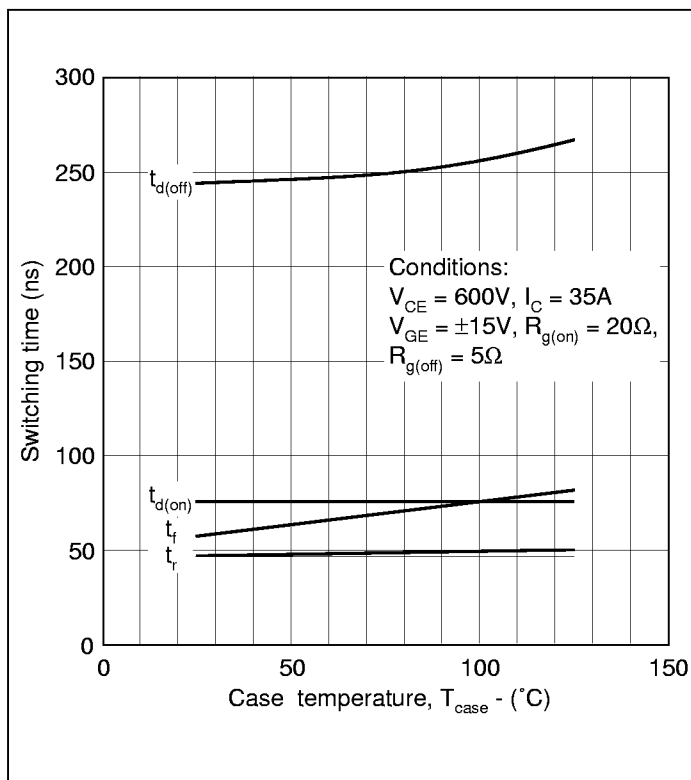


Fig.13 Typical switching times vs case temperature

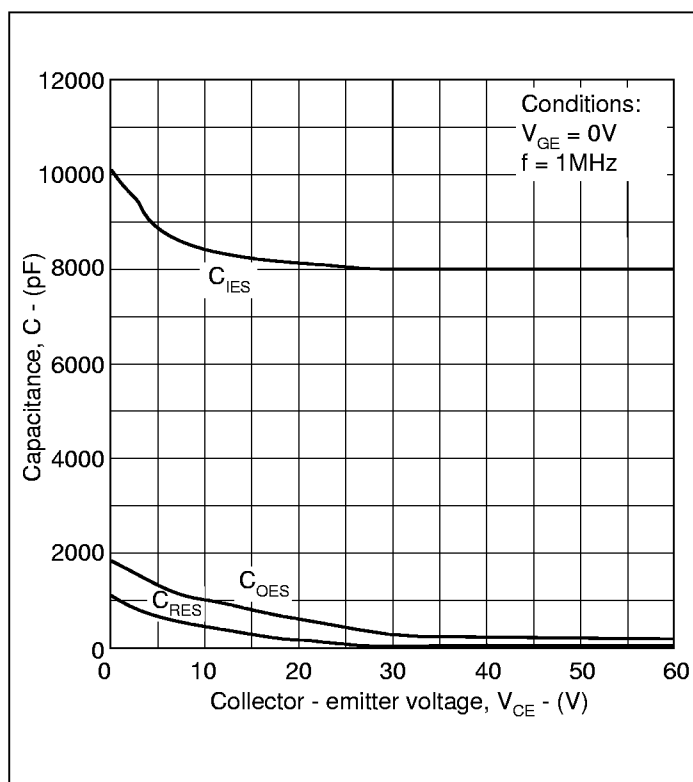


Fig.14 Typical capacitance

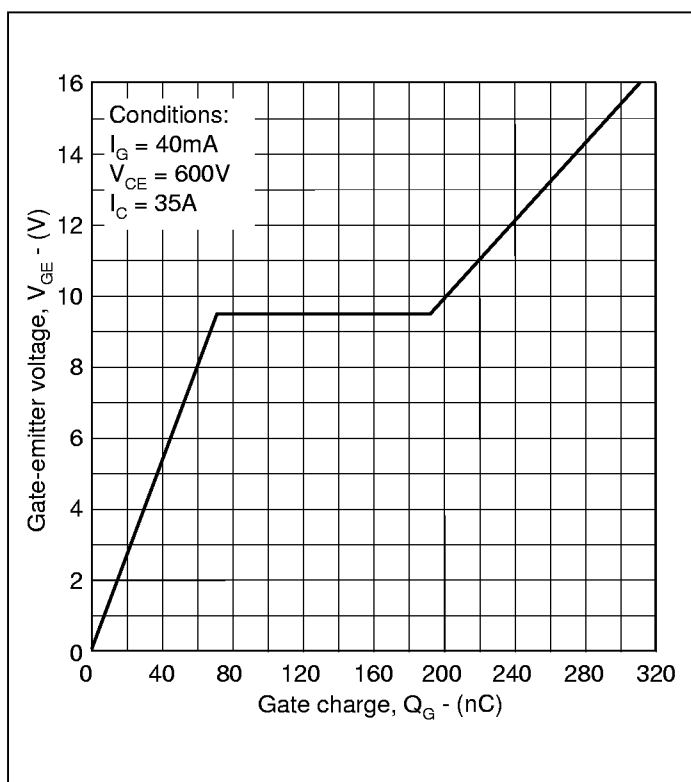


Fig.15 Typical gate charge

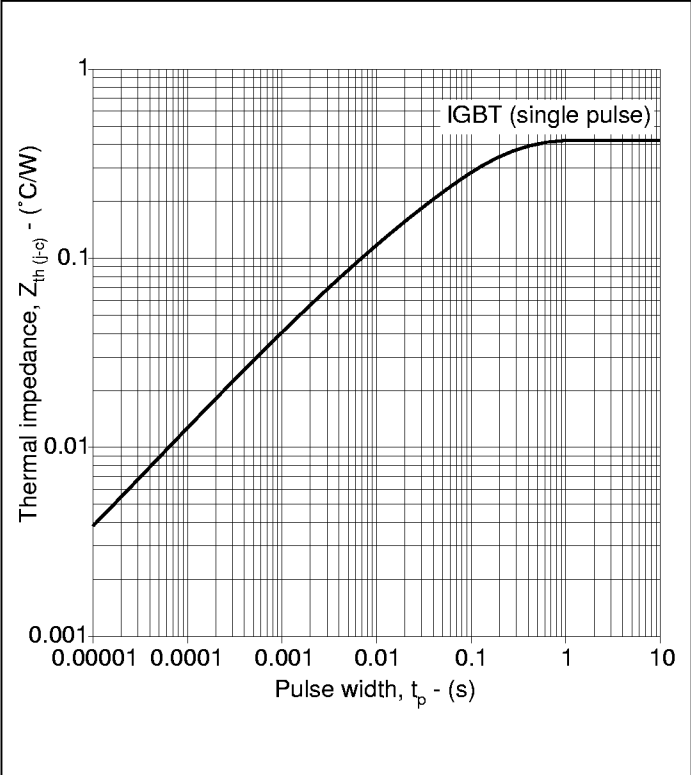


Fig.16 Transient thermal impedance - junction to case

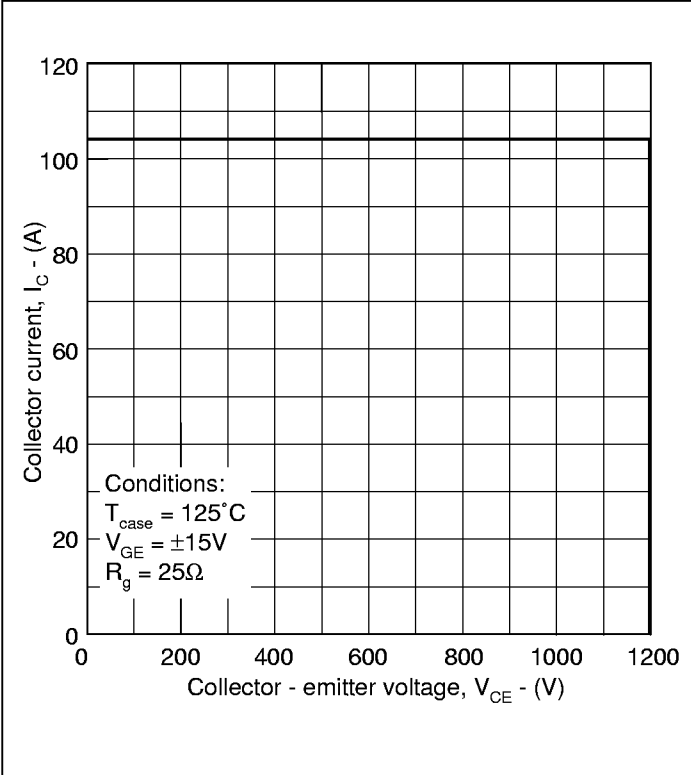


Fig.17 Reverse bias safe operating area

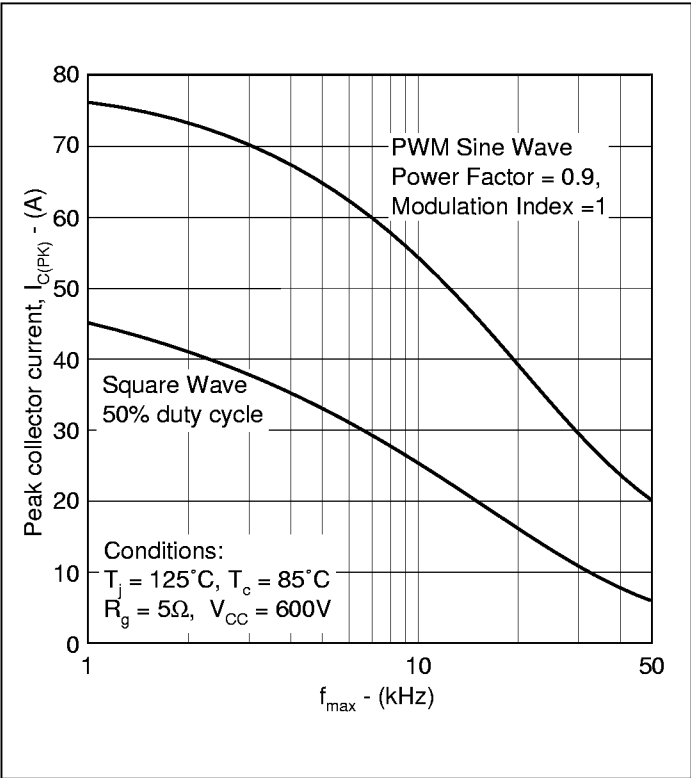


Fig.18 Three Phase PWM inverter operating frequency

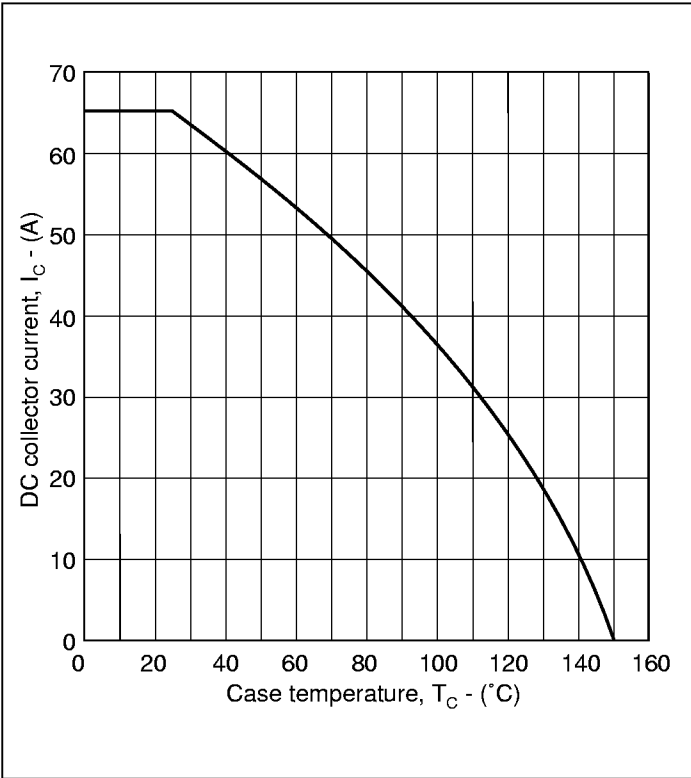


Fig.19 DC current rating vs case temperature

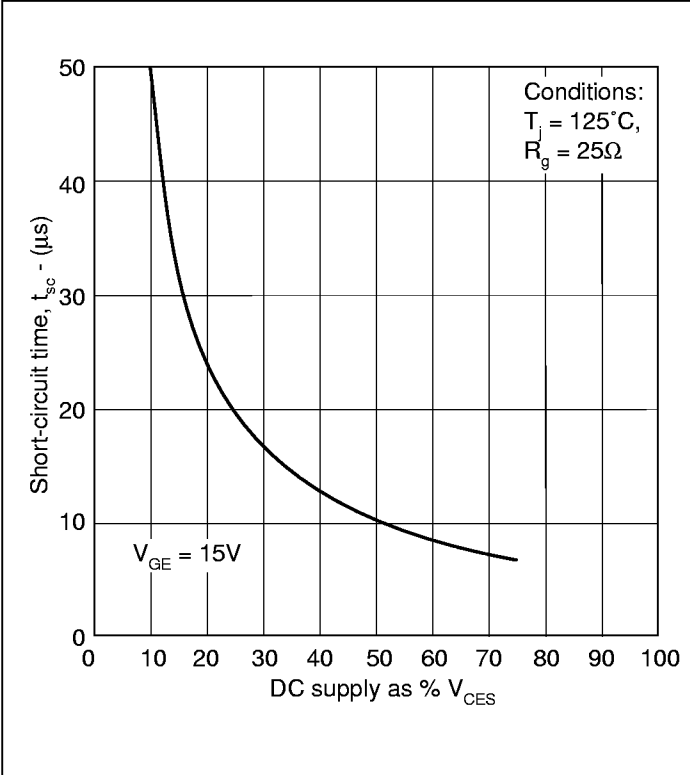


Fig.20 Short circuit withstand

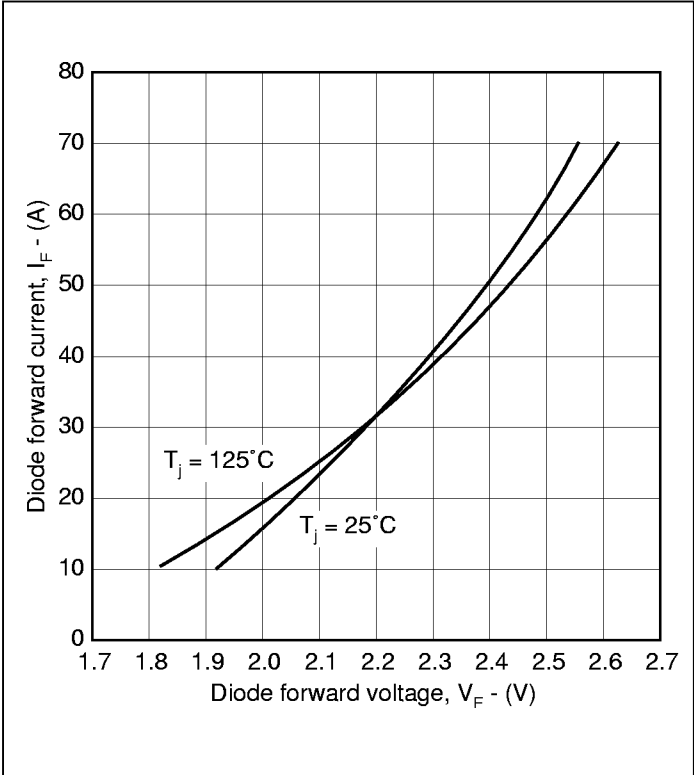
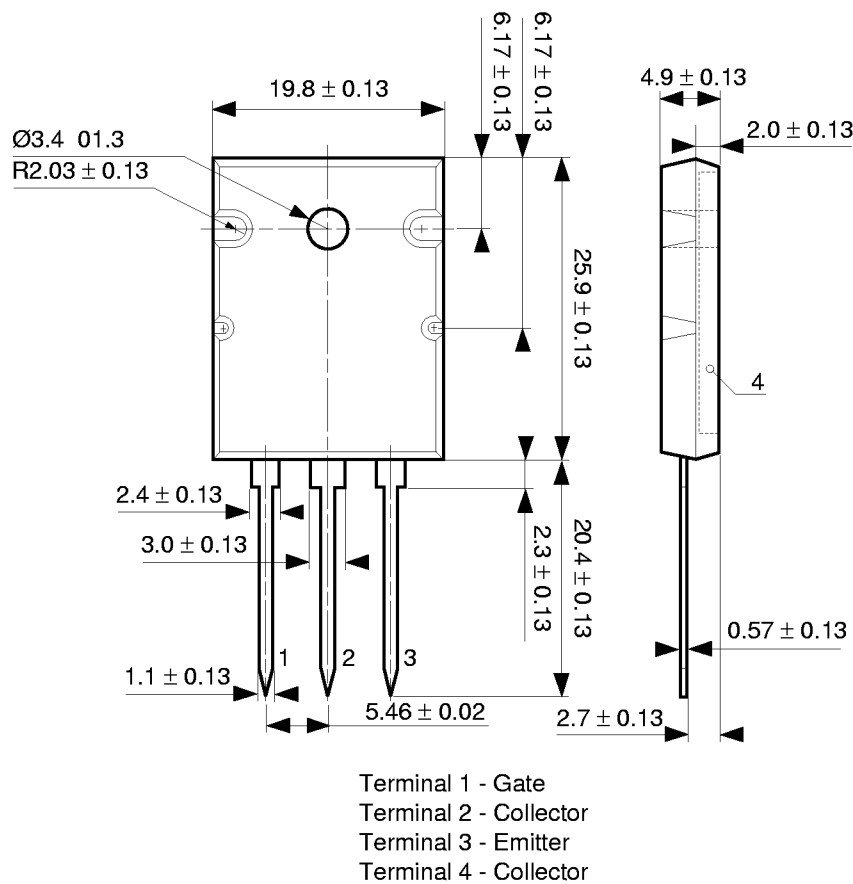


Fig.21 Diode typical forward characteristics

PACKAGE OUTLINE - TO264

For further package information, please contact your local Customer Service Centre. All dimensions in mm, unless stated otherwise. DO NOT SCALE.



HEADQUARTERS POWER OPERATIONS
MITEL SEMICONDUCTOR
Doddington Road, Lincoln,
LN6 3LF, United Kingdom.
Tel: + 44 (0)1522 500500
Fax: + 44 (0)1522 500550

Internet: <http://www.mitelsemi.com>
e-mail: power_solutions@mitel.com
POWER PRODUCT CUSTOMER SERVICE CENTRES
● FRANCE, BENELUX & SPAIN Tel: + 33 (0)1 69 18 90 00 Fax : +33 (0)1 64 46 54 50
● NORTH AMERICA Tel: 011-800-5554-5554 Fax: 011-800-5444-5444
● UK, GERMANY, REST OF WORLD Tel: + 44 (0)1522 500500 Fax : + 44 (0)1522 500020

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